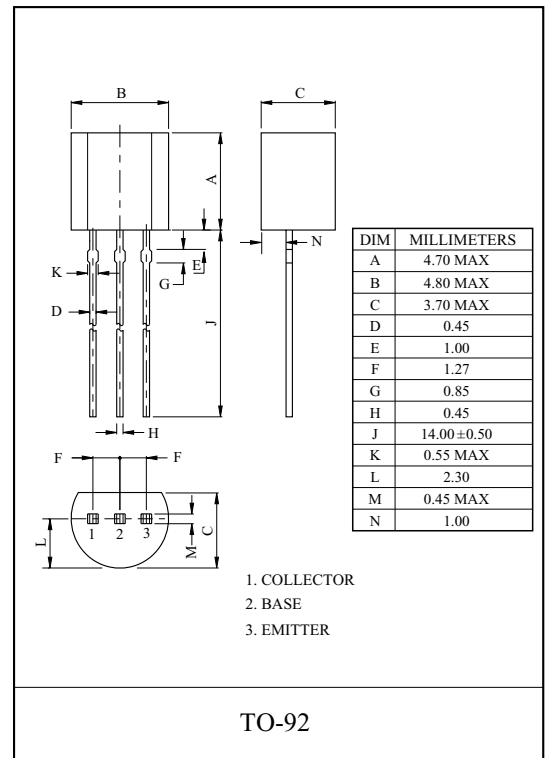


GENERAL PURPOSE HIGH DARLINGTON TRANSISTOR.

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-10	V
Collector Current	I_C	-500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1.0mA, I_C = 0$	-10	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -40V, I_E = 0$	-	-	-1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -10V, I_C = 0$	-	-	-1.0	μA
DC Current Gain	h_{FE}	$I_C = -100mA, V_{CE} = -2V$	30k	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -1mA$	-	-	-1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -1mA$	-	-1.5	-2.0	V
Current Gain Bandwidth Product	f_T	$I_C = -100mA, V_{CE} = -2V, f = 100MHz$	-	220	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz, I_E = 0$	-	5.0	-	pF